
2SK2925(L), 2SK2925(S)

Silicon N Channel MOS FET
High Speed Power Switching

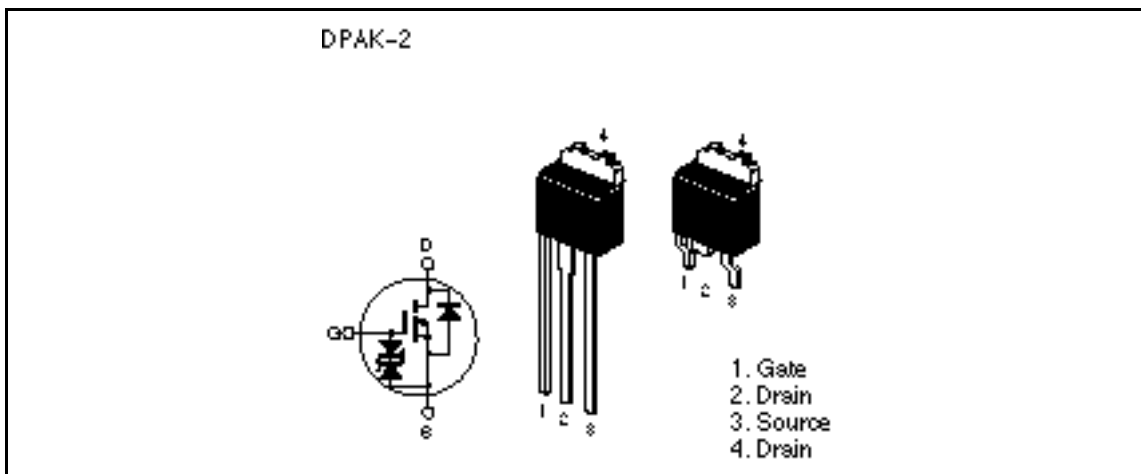
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ADE-208-549
Target Specification 1st. Edition

Features

- Low on-resistance
 $R_{DS} = 0.060$ typ.
- High speed switching
- 4V gate drive device can be driven from 5V source

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	10	A
Drain peak current	$I_{D(pulse)}^{*1}$	40	A
Body to drain diode reverse drain current	I_{DR}	10	A
Avalanche current	I_{AP}^{*3}	10	A
Avalanche energy	E_{AR}^{*3}	8.5	mJ
Channel dissipation	P_{ch}^{*2}	20	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW 10μs, duty cycle 1 %

2. Value at Tc = 25°C

3. Value at Tch = 25°C, Rg 50

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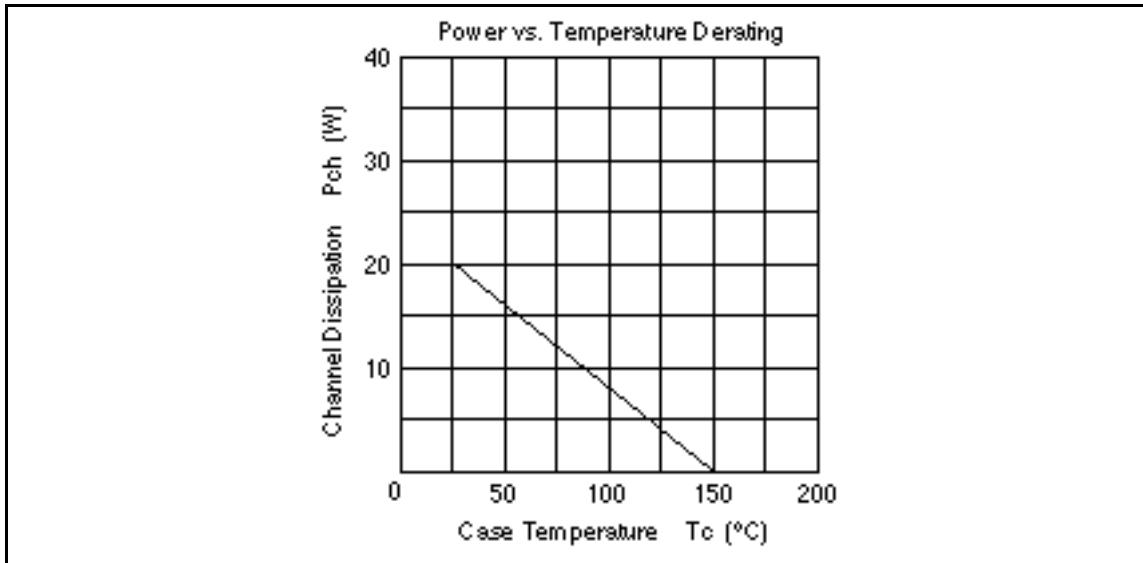
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10\text{mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 20	—	—	V	$I_G = \pm 100\mu\text{A}, V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60\text{V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	2.5	V	$I_D = 1\text{mA}, V_{DS} = 10\text{V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.060	0.080		$I_D = 5\text{A}, V_{GS} = 10\text{V}^{*1}$
	$R_{DS(on)}$	—	0.095	0.160		$I_D = 5\text{A}, V_{GS} = 4\text{V}^{*1}$
Forward transfer admittance	$ y_{fs} $	5	8	—	S	$I_D = 5\text{A}, V_{DS} = 10\text{V}^{*1}$
Input capacitance	C_{iss}	—	350	—	pF	$V_{DS} = 10\text{V}$
Output capacitance	C_{oss}	—	190	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	70	—	pF	$f = 1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	$I_D = 5\text{A}, V_{GS} = 10\text{V}$
Rise time	t_r	—	55	—	ns	$R_L = 6$
Turn-off delay time	$t_{d(off)}$	—	60	—	ns	
Fall time	t_f	—	70	—	ns	
Body to drain diode forward voltage	V_{DF}	—	0.9	—	V	$I_F = 10\text{A}, V_{GS} = 0$
Body to drain diode reverse recovery time	t_{rr}	—	50	—	ns	$I_F = 10\text{A}, V_{GS} = 0$ $diF/dt = 50\text{A}/\mu\text{s}$

Note: 1. Pulse test

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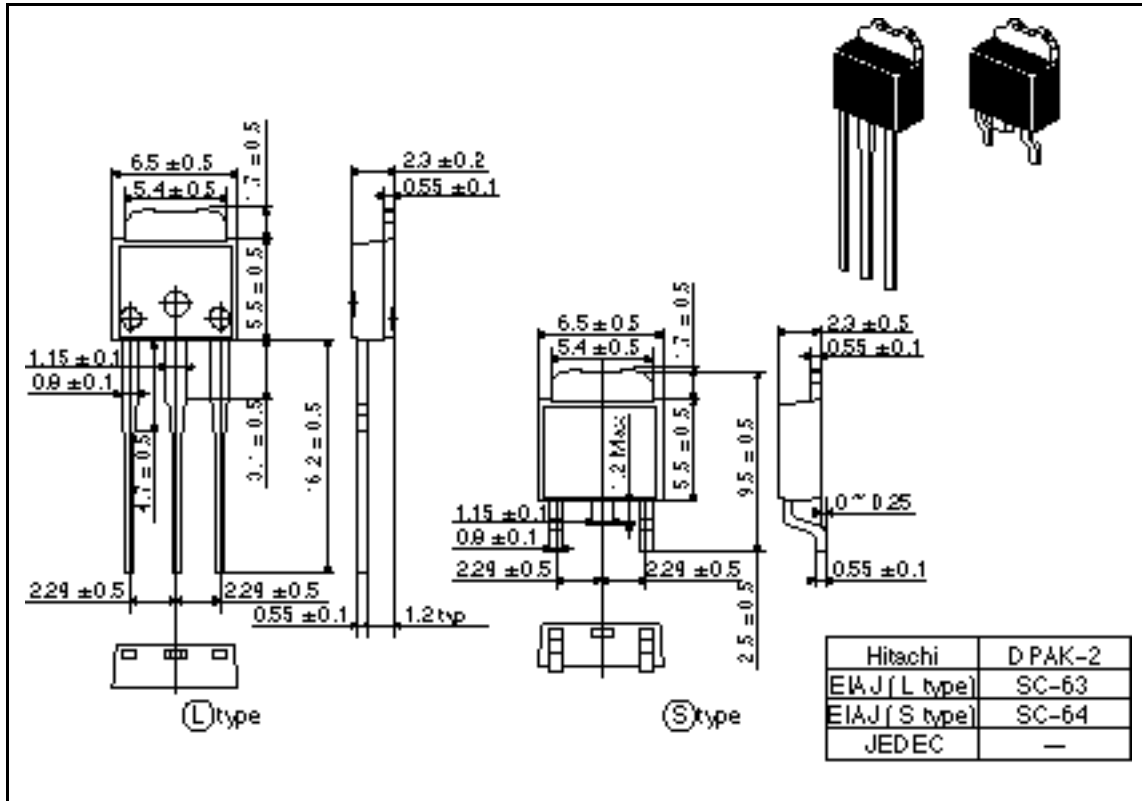
Main Characteristics



2SK2925(L), 2SK2925(S)

Package Dimensions

Unit: mm



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Hitachi, Ltd.

Semiconductor & IC Div.

Nippon Bldg., 2-5-2, Ohite-machi, Chiyoda-ku, Tokyo 100, Japan

Tel: Tokyo (03) 3270-2111

Fax: (03) 3270-5109

For further information write to:

Hitachi America, Ltd.
Semiconductor & IC Div.
2000 Sierra Point Parkway
Brisbane, CA 94005-4835
U.S.A.
Tel: 415-589-8000
Fax: 415-589-4207

Hitachi Europe GmbH
Electronic Components Group
Continental Europe
Dornacher Straße 3
D-85622 Feldkirchen
München
Tel: 089-9 94 80-0
Fax: 089-9 29 30 00

Hitachi Europe Ltd.
Electronic Components Div.
Northern Europe Headquarters
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA
United Kingdom
Tel: 0628-585000
Fax: 0628-778322

Hitachi Asia Pte. Ltd.
45 Collyer Quay #20-00
Hitachi Tower
Singapore 0104
Tel: 535-2100
Fax: 535-1533

Hitachi Asia (Hong Kong) Ltd.
Unit 705, North Tower,
World Finance Centre
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon
Hong Kong
Tel: 27359218
Fax: 27308074

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